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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

E·XFI

Product Status	Obsolete
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, Cap Sense, LCD, LVD, POR, PWM, SmartSense, WDT
Number of I/O	21
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 8x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	25-UFBGA, WLCSP
Supplier Device Package	25-WLCSP (2.07×2.11)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4246fni-d412t

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



More Information

Cypress provides a wealth of data at www.cypress.com to help you to select the right PSoC device for your design, and to help you to quickly and effectively integrate the device into your design. For a comprehensive list of resources, see the knowledge base article KBA86521, How to Design with PSoC 3, PSoC 4, and PSoC 5LP. Following is an abbreviated list for PSoC 4:

- Overview: PSoC Portfolio, PSoC Roadmap
- Product Selectors: PSoC 1, PSoC 3, PSoC 4, PSoC 5LP In addition, PSoC Creator includes a device selection tool.
- Application notes: Cypress offers a large number of PSoC application notes covering a broad range of topics, from basic to advanced level. Recommended application notes for getting started with PSoC 4 are:
 - □ AN79953: Getting Started With PSoC 4
 - □ AN88619: PSoC 4 Hardware Design Considerations
 - □ AN86439: Using PSoC 4 GPIO Pins
 - D AN57821: Mixed Signal Circuit Board Layout
 - □ AN81623: Digital Design Best Practices
 - □ AN73854: Introduction To Bootloaders
 - AN89610: ARM Cortex Code Optimization

- Technical Reference Manual (TRM) is in two documents:
- □ Architecture TRM details each PSoC 4 functional block.
- □ Registers TRM describes each of the PSoC 4 registers.
- Development Kits:
 - CY8CKIT-042, PSoC 4 Pioneer Kit, is an easy-to-use and inexpensive development platform. This kit includes connectors for Arduino[™] compatible shields and Digilent® Pmod[™] daughter cards.
 - CY8CKIT-049 is a very low-cost prototyping platform. It is a low-cost alternative to sampling PSoC 4 devices.
 - CY8CKIT-001 is a common development platform for any one of the PSoC 1, PSoC 3, PSoC 4, or PSoC 5LP families of devices.

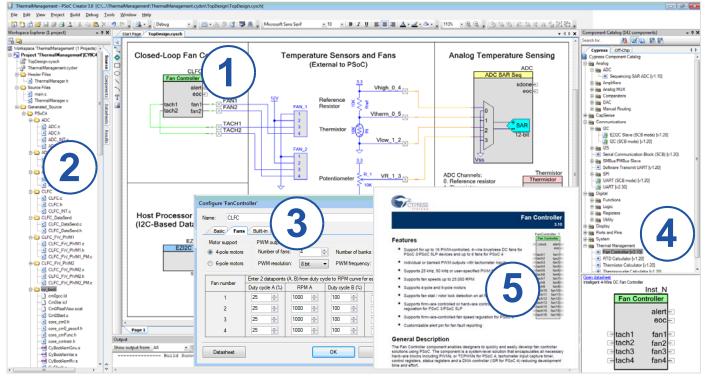
The MiniProg3 device provides an interface for flash programming and debug.

PSoC Creator

PSoC Creator is a free Windows-based Integrated Design Environment (IDE). It enables concurrent hardware and firmware design of PSoC 3, PSoC 4, and PSoC 5LP based systems. Create designs using classic, familiar schematic capture supported by over 100 pre-verified, production-ready PSoC Components; see the list of component datasheets. With PSoC Creator, you can:

- 1. Drag and drop component icons to build your hardware system design in the main design workspace
- 2. Codesign your application firmware with the PSoC hardware, using the PSoC Creator IDE C compiler
- 3. Configure components using the configuration tools
- 4. Explore the library of 100+ components
- 5. Review component datasheets







Functional Definition

CPU and Memory Subsystem

CPU

The Cortex-M0 CPU in the PSoC 4200-L is part of the 32-bit MCU subsystem, which is optimized for low-power operation with extensive clock gating. Most instructions are 16 bits in length and execute a subset of the Thumb-2 instruction set. This enables fully compatible binary upward migration of the code to higher performance processors such as the Cortex-M3 and M4, thus enabling upward compatibility. The Cypress implementation includes a hardware multiplier that provides a 32-bit result in one cycle. It includes a nested vectored interrupt controller (NVIC) block with 32 interrupt inputs and also includes a Wakeup Interrupt Controller (WIC), which can wake the processor up from the Deep Sleep mode allowing power to be switched off to the main processor when the chip is in the Deep Sleep mode. The Cortex-M0 CPU provides a Non-Maskable Interrupt (NMI) input, which is made available to the user when it is not in use for system functions requested by the user.

The CPU also includes a debug interface, the serial wire debug (SWD) interface, which is a 2-wire form of JTAG; the debug configuration used for PSoC 4200-L has four break-point (address) comparators and two watchpoint (data) comparators.

Flash

The PSoC 4200-L has a flash module with a flash accelerator, tightly coupled to the CPU to improve average access times from the flash block. The flash block is designed to deliver 2 wait-state (WS) access time at 48 MHz and with 1-WS access time at 24 MHz. The flash accelerator delivers 85% of single-cycle SRAM access performance on average. Part of the flash module can be used to emulate EEPROM operation if required.

SRAM

SRAM memory is retained during Hibernate.

SROM

A supervisory ROM that contains boot and configuration routines is provided.

DMA

A DMA engine is provided that can do 32-bit transfers and has chainable ping-pong descriptors.

System Resources

Power System

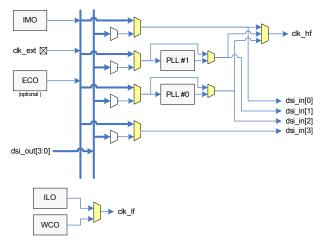
The power system is described in detail in the section Power on page 15. It provides assurance that voltage levels are as required for each respective mode and either delay mode entry (on power-on reset (POR), for example) until voltage levels are as required for proper function or generate resets (brown-out detect (BOD)) or interrupts (low voltage detect (LVD)). The PSoC 4200-L operates with a single external supply over the range of 1.71 to 5.5 V and has five different power modes, transitions between which are managed by the power system. The PSoC 4200-L provides Sleep, Deep Sleep, Hibernate, and Stop low-power modes.

Clock System

The PSoC 4200-L clock system is responsible for providing clocks to all subsystems that require clocks and for switching between different clock sources without glitching. In addition, the clock system ensures that no meta-stable conditions occur.

The clock system for the PSoC 4200-L consists of a crystal oscillator (4 to 33 MHz), a watch crystal oscillator (32 kHz), a phase-locked loop (PLL), the IMO and the ILO internal oscillators, and provision for an external clock.





The clk_hf signal can be divided down to generate synchronous clocks for the UDBs, and the analog and digital peripherals. There are a total of 16 clock dividers for the PSoC 4200-L, each with 16-bit divide capability; this allows 12 to be used for the fixed-function blocks and four for the UDBs. The analog clock leads the digital clocks to allow analog events to occur before digital clock-related noise is generated. The 16-bit capability allows a lot of flexibility in generating fine-grained frequency values and is fully supported in PSoC Creator.

IMO Clock Source

The IMO is the primary source of internal clocking in the PSoC 4200-L. It is trimmed during testing to achieve the specified accuracy. Trim values are stored in nonvolatile latches (NVL). Additional trim settings from flash can be used to compensate for changes. The IMO default frequency is 24 MHz and it can be adjusted between 3 to 48 MHz in steps of 1 MHz. IMO tolerance with Cypress-provided calibration settings is ±2%.

ILO Clock Source

The ILO is a very low power oscillator, nominally 32 kHz, which is primarily used to generate clocks for peripheral operation in Deep Sleep mode. ILO-driven counters can be calibrated to the IMO to improve accuracy. Cypress provides a software component, which does the calibration.

Crystal Oscillators and PLL

The PSoC 4200-L clock subsystem also implements two oscillators: high-frequency (4 to 33 MHz) and low-frequency (32-kHz watch crystal) that can be used for precision timing applications. The PLL can generate a 48-MHz output from the high-frequency oscillator.



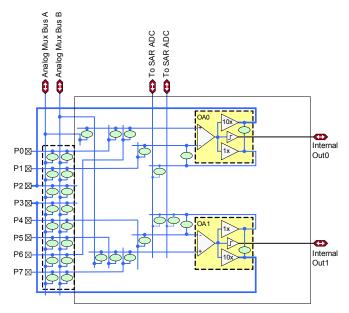
Analog Multiplex Bus

The PSoC4200-L has two concentric analog buses (Analog Mux Bus A and Analog Mux Bus B) that circumnavigate the periphery of the chip. These buses can transport analog signals from any pin to various analog blocks (including the opamps) and to the CapSense blocks allowing, for instance, the ADC to monitor any pin on the chip. These buses are independent and can also be split into three independent sections. This allows one section to be used for CapSense purposes, one for general analog signal processing, and the third for general-purpose digital peripherals and GPIO.

Four Opamps (CTBm Blocks)

The PSoC 4200-L has four opamps with Comparator modes, which allow most common analog functions to be performed on-chip eliminating external components; PGAs, voltage buffers, filters, trans-impedance amplifiers, and other functions can be realized with external passives saving power, cost, and space. The on-chip opamps are designed with enough bandwidth to drive the Sample-and-Hold circuit of the ADC without requiring external buffering. The opamps can operate in the Deep Sleep mode at very low power levels. The following diagram shows one of two identical opamp pairs of the opamp subsystem.

Figure 5. Identical Opamp Pairs in Opamp Subsystem



The ovals in Figure 5 represent analog switches, which may be controlled via user firmware, the SAR sequencer, or user-defined programmable logic. The opamps (OA0 and OA1) are configurable via these switches to perform all standard opamp functions with appropriate feedback components.

The opamps (OA0 and OA1) are programmable and reconfigurable to provide standard opamp functionality via switchable feedback components, unity gain functionality for driving pins directly, or for internal use (such as buffering SAR ADC inputs as indicated in the diagram), or as true comparators.

The opamp inputs provide highly flexible connectivity and can connect directly to dedicated pins or, via the analog mux buses,

The opamps operate in Deep Sleep mode at very low currents allowing analog circuits to remain operational during Deep Sleep.

Temperature Sensor

The PSoC 4200-L has one on-chip temperature sensor. This consists of a diode, which is biased by a current source that can be disabled to save power. The temperature sensor is connected to the ADC, which digitizes the reading and produces a temperature value using Cypress-supplied software that includes calibration and linearization.

Low-power Comparators

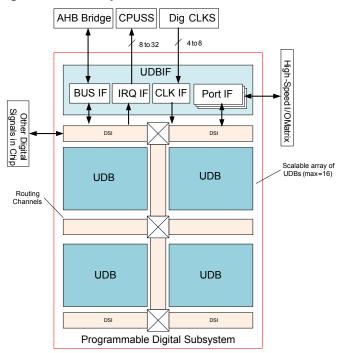
The PSoC 4200-L has a pair of low-power comparators, which can also operate in the Deep Sleep and Hibernate modes. This allows the analog system blocks to be disabled while retaining the ability to monitor external voltage levels during low-power modes. The comparator outputs are normally synchronized to avoid meta-stability unless operating in an asynchronous power mode (Hibernate) where the system wake-up circuit is activated by a comparator switch event.

Programmable Digital

Universal Digital Blocks (UDBs) and Port Interfaces

The PSoC 4200-L has eight UDBs; the UDB array also provides a switched Digital System Interconnect (DSI) fabric that allows signals from peripherals and ports to be routed to and through the UDBs for communication and control. The UDB array is shown in the following figure.

Figure 6. UDB Array





Port/Pin	Analog	PRGIO & USB	Alt. Function 1	Alt. Function 2	Alt. Function 3	Alt. Function 4	Alt. Function 5
P4.2	csd[0].c_mod			scb[0].uart_cts:2	can[0].can_tx_enb_ lpcomp.comp[0]:2 n:1		scb[0].spi_clk:2
P4.3	csd[0].c_sh_tank			scb[0].uart_rts:2		lpcomp.comp[1]:2	scb[0].spi_select0:2
P4.4					can[1].can_tx_enb_ n:1		scb[0].spi_select1:2
P4.5					can[1].can_rx:1		scb[0].spi_select2:2
P4.6					can[1].can_tx:1		scb[0].spi_select3:2
P4.7							
P13.0		USBDP					
P13.1		USBDM					
P13.2		VBUS					
P7.0	srss.eco_in		tcpwm.line[0]:3	scb[3].uart_rx:2		scb[3].i2c_scl:2	scb[3].spi_mosi:2
P7.1	srss.eco_out		tcpwm.line_compl[0]:3	scb[3].uart_tx:2		scb[3].i2c_sda:2	scb[3].spi_miso:2
P7.2			tcpwm.line[1]:3	scb[3].uart_cts:2			scb[3].spi_clk:2
P7.3			tcpwm.line_compl[1]:3	scb[3].uart_rts:2			scb[3].spi_select0:2
P7.4			tcpwm.line[2]:3				scb[3].spi_select1:2
P7.5			tcpwm.line_compl[2]:3				scb[3].spi_select2:2
P7.6			tcpwm.line[3]:3				scb[3].spi_select3:2
P7.7			tcpwm.line_compl[3]:3				

Descriptions of the power pin functions are as follows:

VDDD: Power supply for both analog and digital sections (where there is no V_{DDA} pin)

VDDA: Analog V_{DD} pin where package pins allow; shorted to V_{DDD} otherwise

VDDIO: I/O pin power domain

VSSA: Analog ground pin where package pins allow; shorted to VSS otherwise

VSS: Ground pin

VCCD: Regulated digital supply (1.8 V ±5%)

GPIO and GPIO_OVT pins can be used as CSD sense and shield pins (a total of 94). Up to 64 of the pins can be used for LCD drive.

The following packages are supported: 124-ball BGA, 64-pin TQFP, 68-pin QFN, and 48-pin TQFP.

Power

The supply voltage range is 1.71 V to 5.5 V with all functions and circuits operating over that range.

The PSoC 4200-L family allows two distinct modes of power supply operation: Unregulated External Supply and Regulated External Supply modes.

Unregulated External Supply

In this mode, the PSoC 4200-L is powered by an External Power Supply that can be anywhere in the range of 1.8 V to 5.5 V. This range is also designed for battery-powered operation, for instance, the chip can be powered from a battery system that starts at 3.5 V and works down to 1.8 V. In this mode, the internal regulator of the PSoC 4200-L supplies the internal logic and the VCCD output of the PSoC 4200-L must be bypassed to ground via an external Capacitor (in the range of 1 to 1.6 μ F; X5R ceramic or better).

VDDA and VDDD must be shorted together on the PC board; the grounds, VSSA and VSS must also be shorted together. Bypass capacitors must be used from VDDD and VDDA to ground, typical practice for systems in this frequency range is to use a capacitor in the 1 μ F range in parallel with a smaller capacitor (0.1 μ F, for example). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

Power Supply	Bypass Capacitors
VDDD–VSS and VDDIO-VSS	0.1 μ F ceramic at each pin plus bulk capacitor 1 to 10 μ F.
VDDA-VSSA	0.1 μ F ceramic at pin. Additional 1 μ F to 10 μ F bulk capacitor
VCCD-VSS	1 µF ceramic capacitor at the VCCD pin
VREF–VSSA (optional)	The internal bandgap may be bypassed with a 1 μ F to 10 μ F capacitor for better ADC performance.

Regulated External Supply

In this mode, the PSoC 4200-L is powered by an external power supply that must be within the range of 1.71 V to 1.89 V ($1.8 \pm 5\%$); note that this range needs to include power supply ripple. In this mode, the VCCD and VDDD pins are shorted together and bypassed. The internal regulator is disabled in firmware.



Electrical Specifications

Absolute Maximum Ratings

Table 1. Absolute Maximum Ratings^[1]

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID1	V _{DD_ABS}	Analog or digital supply relative to V_{SS} ($V_{SSD} = V_{SSA}$)	-0.5	-	6	V	Absolute maximum
SID2	V _{CCD_ABS}	Direct digital core voltage input relative to V_{SSD}	-0.5	-	1.95	V	Absolute maximum
SID3	V _{GPIO_ABS}	GPIO voltage; V _{DDD} or V _{DDA}	-0.5	-	V _{DD} +0.5	V	Absolute maximum
SID4	I _{GPIO_ABS}	Current per GPIO	-25	-	25	mA	Absolute maximum
SID5	I _{G-PIO_injection}	GPIO injection current per pin	-0.5	-	0.5	mA	Absolute maximum
BID44	ESD_HBM	Electrostatic discharge human body model	2200	-	-	V	
BID45	ESD_CDM	Electrostatic discharge charged device model	500	-	-	V	
BID46	LU	Pin current for latch-up	-140	_	140	mA	

Device Level Specifications

All specifications are valid for -40 °C \leq TA \leq 85 °C and TJ \leq 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 2. DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
SID53	V _{DDD}	Power Supply Input Voltage ($V_{DDA} = V_{DDD} = V_{DD}$)	1.8	_	5.5	V	With regulator enabled
SID255	V _{DDD}	Power supply input voltage unregulated	1.71	1.8	1.89	V	Internally unregu- lated Supply
SID54	V _{CCD}	Output voltage (for core logic)	_	1.8	_	V	
SID55	C _{EFC}	External regulator voltage bypass	1	1.3	1.6	μF	X5R ceramic or better
SID56	C _{EXC}	Power supply decoupling capacitor	_	1	-	μF	X5R ceramic or better
Active Mode							·
SID6	I _{DD1}	Execute from flash; CPU at 6 MHz	-	2.2	3.1	mA	
SID7	I _{DD2}	Execute from flash; CPU at 12 MHz	_	3.7	4.8	mA	
SID8	I _{DD3}	Execute from flash; CPU at 24 MHz	_	6.7	8.0	mA	
SID9	I _{DD4}	Execute from flash; CPU at 48 MHz	_	12.8	14.5	mA	
Sleep Mode							
SID21	I _{DD16}	I ² C wakeup, WDT, and Comparators on. Regulator Off.	-	1.8	2.2	mA	V _{DD} = 1.71 to 1.89, 6 MHz
SID22	I _{DD17}	I ² C wakeup, WDT, and Comparators on.	_	1.7	2.1	mA	V _{DD} = 1.8 to 5.5, 6 MHz

Note

Usage above the absolute maximum conditions listed in Table 1 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.



Table 2. DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
SID23	I _{DD18}	I ² C wakeup, WDT, and Comparators on. Regulator Off.	_	2.4	2.9	mA	V _{DD} = 1.71 to 1.89, 12 MHz
SID24	I _{DD19}	I ² C wakeup, WDT, and Comparators on.	-	2.3	2.8	mA	V _{DD} = 1.8 to 5.5, 12 MHz
Deep Sleep I	Mode, –40 °C to	+ 60 °C					
SID30	I _{DD25}	I ² C wakeup and WDT on. Regulator Off.	_	-	13.5	μA	V _{DD} = 1.71 to 1.89
SID31	I _{DD26}	I ² C wakeup and WDT on.	-	1.3	20.0	μA	V _{DD} = 1.8 to 3.6
SID32	I _{DD27}	I ² C wakeup and WDT on.	-	-	20.0	μA	V _{DD} = 3.6 to 5.5
Deep Sleep I	Mode, +85 °C	· · · ·					
SID33	I _{DD28}	I ² C wakeup and WDT on. Regulator Off.	-	-	45.0	μA	V _{DD} = 1.71 to 1.89
SID34	I _{DD29}	I ² C wakeup and WDT on.	-	15	60.0	μA	V _{DD} = 1.8 to 3.6
SID35	I _{DD30}	I ² C wakeup and WDT on.	-	-	45.0	μA	V _{DD} = 3.6 to 5.5
Hibernate Mo	ode, -40 °C to +	60 °C					
SID39	I _{DD34}	Regulator Off.	-	_	1123	nA	V _{DD} = 1.71 to 1.89
SID40	I _{DD35}		_	150	1600	nA	V _{DD} = 1.8 to 3.6
SID41	I _{DD36}		-	_	1600	nA	V _{DD} = 3.6 to 5.5
Hibernate Mo	ode, +85 °C	· · · ·					
SID42	I _{DD37}	Regulator Off.	-	_	4142	nA	V _{DD} = 1.71 to 1.89
SID43	I _{DD38}		_	-	9700	nA	V _{DD} = 1.8 to 3.6
SID44	I _{DD39}		-	-	10,400	nA	V _{DD} = 3.6 to 5.5
Stop Mode	·						<u>.</u>
SID304	I _{DD43A}	Stop Mode current; V _{DD} = 3.6 V	_	20	659	nA	T = -40 °C to $+60$ °C
SID304A	I _{DD43B}	Stop Mode current; V _{DD} = 3.6 V	-	-	1810	nA	T = +85 °C
XRES curren	nt						
SID307	I _{DD_XR}	Supply current while XRES (Active Low) asserted	-	2	5	mA	

Table 3. AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID48	F _{CPU}	CPU frequency	DC	-	48	MHz	$1.71 \leq V_{DD} \leq 5.5$
SID49	T _{SLEEP}	Wakeup from sleep mode	-	0	_	μs	Guaranteed by characterization
SID50	T _{DEEPSLEEP}	Wakeup from Deep Sleep mode	-	-	25	μs	24-MHz IMO. Guaranteed by characterization
SID51	T _{HIBERNATE}	Wakeup from Hibernate mode	-	-	0.7	ms	Guaranteed by characterization
SID51A	T _{STOP}	Wakeup from Stop mode	-	-	1.9	ms	Guaranteed by characterization
SID52	T _{RESETWIDTH}	External reset pulse width	1	-	_	μs	Guaranteed by characterization



GPIO

Table 4. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID57	V _{IH} ^[2]	Input voltage high threshold	0.7 × V _{DDD}	-	-	V	CMOS Input
SID57A	I _{IHS}	Input current when Pad > V _{DDIO} for OVT inputs	-	-	10	μA	Per I ² C Spec
SID58	V _{IL}	Input voltage low threshold	-	-	0.3 × V _{DDD}	V	CMOS Input
SID241	V _{IH} [2]	LVTTL input, V _{DDD} < 2.7 V	0.7× V _{DDD}	-	-	V	
SID242	V _{IL}	LVTTL input, V _{DDD} < 2.7 V	-	-	0.3 × V _{DDD}	V	
SID243	V _{IH} [2]	LVTTL input, $V_{DDD} \ge 2.7 V$	2.0	-	_	V	
SID244	V _{IL}	LVTTL input, $V_{DDD} \ge 2.7 V$	-	-	0.8	V	
SID59	V _{OH}	Output voltage high level	V _{DDD} -0.6	-	_	V	I _{OH} = 4 mA at 3 V V _{DDD}
SID60	V _{OH}	Output voltage high level	V _{DDD} -0.5	-	-	V	I _{OH} = 1 mA at 1.8 V V _{DDD}
SID61	V _{OL}	Output voltage low level	-	-	0.6	V	I _{OL} = 4 mA at 1.8 V V _{DDD}
SID62	V _{OL}	Output voltage low level	-	-	0.6	V	I _{OL} = 8 mA at 3 V V _{DDD}
SID62A	V _{OL}	Output voltage low level	-	-	0.4	V	I _{OL} = 3 mA at 3 V V _{DDD}
SID63	R _{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	
SID64	R _{PULLDOWN}	Pull-down resistor	3.5	5.6	8.5	kΩ	
SID65	IIL	Input leakage current (absolute value)	-	-	2	nA	25 °C, V _{DDD} = 3.0 V
SID65A	I _{IL_CTBM}	Input leakage current (absolute value) for CTBM pins	-	-	4	nA	
SID66	C _{IN}	Input capacitance	-	_	7	pF	Not applicable for P6.4, P6.5, P12.0, P12.1, and for USB pins.
SID67	V _{HYSTTL}	Input hysteresis LVTTL	25	40	_	mV	$V_{DDD} \ge 2.7 \text{ V}$
SID68	V _{HYSCMOS}	Input hysteresis CMOS	0.05 × V _{DDD}	-	_	mV	
SID69	I _{DIODE}	Current through protection diode to V _{DD} /Vss	-	-	100	μA	Guaranteed by characterization
SID69A	I _{TOT_GPIO}	Maximum Total Source or Sink Chip Current	-	-	200	mA	Guaranteed by characterization



Analog Peripherals

Opamp

Table 8. Opamp Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
	I _{DD}	Opamp block current. No load.	-	-	-	_	
SID269	I _{DD_HI}	Power = high	-	1100	1850	μA	
SID270	I _{DD_MED}	Power = medium	-	550	950	μA	
SID271	I _{DD_LOW}	Power = low	-	150	350	μA	
	GBW	Load = 20 pF, 0.1 mA. V _{DDA} = 2.7 V	-	_	-	_	
SID272	GBW_HI	Power = high	6	-	-	MHz	
SID273	GBW_MED	Power = medium	4	_	-	MHz	
SID274	GBW_LO	Power = low	-	1	-	MHz	
	I _{OUT_MAX}	$V_{DDA} \ge 2.7 \text{ V}, 500 \text{ mV}$ from rail	-	-	-	-	
SID275	I _{OUT_MAX_HI}	Power = high	10	-	-	mA	
SID276	IOUT_MAX_MID	Power = medium	10	-	-	mA	
SID277	IOUT_MAX_LO	Power = low	-	5	-	mA	
	I _{OUT}	V _{DDA} = 1.71 V, 500 mV from rail	-	-	-	_	
SID278	I _{OUT_MAX_HI}	Power = high	4	-	-	mA	
SID279	IOUT_MAX_MID	Power = medium	4	-	-	mA	
SID280	IOUT_MAX_LO	Power = low	-	2	-	mA	
SID281	V _{IN}	Input voltage range	-0.05	-	V _{DDA} - 0.2	V	Charge-pump on, $V_{DDA} \ge 2.7 \text{ V}$
SID282	V _{CM}	Input common mode voltage	-0.05	_	VDDA - 0.2	V	Charge-pump on, $V_{DDA} \ge 2.7 \text{ V}$
	V _{OUT}	$V_{DDA} \ge 2.7 V$	_	_	_		
SID283	V _{OUT_1}	Power = high, I _{load} =10 mA	0.5	_	VDDA - 0.5	V	
SID284	V _{OUT_2}	Power = high, I _{load} =1 mA	0.2	_	VDDA - 0.2	V	
SID285	V _{OUT_3}	Power = medium, I _{load} =1 mA	0.2	_	VDDA - 0.2	V	
SID286	V _{OUT_4}	Power = low, I _{load} =0.1mA	0.2	_	VDDA - 0.2	V	
SID288	V _{OS_TR}	Offset voltage, trimmed	1	±0.5	1	mV	High mode
SID288A	V _{OS_TR}	Offset voltage, trimmed	-	±1	-	mV	Medium mode
SID288B	V _{OS_TR}	Offset voltage, trimmed	-	±2	-	mV	Low mode
SID290	V _{OS_DR_TR}	Offset voltage drift, trimmed	-10	±3	10	μV/°C	High mode
SID290A	V _{OS_DR_TR}	Offset voltage drift, trimmed	-	±10	-	μV/°C	Medium mode
SID290B	V _{OS_DR_TR}	Offset voltage drift, trimmed	-	±10	-	μV/°C	Low mode
SID291	CMRR	DC	60	70	-	dB	V _{DDD} = 3.6 V
SID292	PSRR	At 1 kHz, 100 mV ripple	70	85	-	dB	VDDD = 3.6 V
	Noise		-	_	-	-	
SID293	V _{N1}	Input referred, 1 Hz - 1GHz, power = high	-	94	-	µVrms	
SID294	V _{N2}	Input referred, 1 kHz, power = high	_	72	-	nV/rtHz	



Table 13. SAR ADC AC Specifications

(Guaranteed by Characterization) (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID108B	A_SAMP_3	Sample rate with no bypass cap. Internal reference	-	-	100	ksps	
SID109	A_SNDR	Signal-to-noise and distortion ratio (SINAD)	65	-	-	dB	F _{IN} = 10 kHz
SID111	A_INL	Integral non linearity	-1.7	_	+2	LSB	V _{DD} = 1.71 to 5.5, 1 Msps, Vref = 1 to 5.5.
SID111A	A_INL	Integral non linearity	-1.5	-	+1.7	LSB	V _{DDD} = 1.71 to 3.6, 1 Msps, Vref = 1.71 to V _{DDD} .
SID111B	A_INL	Integral non linearity	-1.5	-	+1.7	LSB	V _{DDD} = 1.71 to 5.5, 500 ksps, Vref = 1 to 5.5.
SID112	A_DNL	Differential non linearity	-1	-	+2.2	LSB	V _{DDD} = 1.71 to 5.5, 1 Msps, Vref = 1 to 5.5.
SID112A	A_DNL	Differential non linearity	–1	_	+2	LSB	V _{DDD} = 1.71 to 3.6, 1 Msps, Vref = 1.71 to V _{DDD} .
SID112B	A_DNL	Differential non linearity	–1	_	+2.2	LSB	V _{DDD} = 1.71 to 5.5, 500 ksps, Vref = 1 to 5.5.
SID113	A_THD	Total harmonic distortion	_	_	-65	dB	F _{IN} = 10 kHz.

CSD

Table 14. CSD Block Specification

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
CSD Spec	ification	-		••		•	•
SID308	VCSD	Voltage range of operation	1.71	_	5.5 V		
SID309	IDAC1	DNL for 8-bit resolution	-1	_	1	LSB	
SID310	IDAC1	INL for 8-bit resolution	-3	_	3	LSB	
SID311	IDAC2	DNL for 7-bit resolution	-1	_	1	LSB	
SID312	IDAC2	INL for 7-bit resolution	-3	_	3	LSB	
SID313	SNR	Ratio of counts of finger to noise. Guaranteed by characterization	5	-	-	Ratio	Capacitance range of 9 to 35 pF, 0.1 pF sensitivity
SID314	IDAC1_CRT1	Output current of Idac1 (8-bits) in High range	-	612	-	μA	
SID314A	IDAC1_CRT2	Output current of Idac1(8-bits) in Low range	-	306	-	μA	
SID315	IDAC2_CRT1	Output current of Idac2 (7-bits) in High range	_	304.8	_	μA	
SID315A	IDAC2_CRT2	Output current of Idac2 (7-bits) in Low range	_	152.4	_	μA	



SPI Specifications

Table 22. Fixed SPI DC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units
SID163	I _{SPI1}	Block current consumption at 1 Mbits/sec	-	_	360	μA
SID164	I _{SPI2}	Block current consumption at 4 Mbits/sec	-	_	560	μA
SID165	I _{SPI3}	Block current consumption at 8 Mbits/sec	-	_	600	μA

Table 23. Fixed SPI AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units
SID166	011	SPI operating frequency (master; 6X oversampling)	-	1	8	MHz

Table 24. Fixed SPI Master Mode AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units
SID167	T _{DMO}	MOSI valid after Sclock driving edge	-	-	15	ns
SID168	T _{DSI}	MISO valid before Sclock capturing edge. Full clock, late MISO Sampling used	20	_	_	ns
SID169	Т _{НМО}	Previous MOSI data hold time with respect to capturing edge at Slave	0	_	_	ns

Table 25. Fixed SPI Slave mode AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units
SID170	T _{DMI}	MOSI valid before Sclock capturing edge	40	-	-	ns
SID171	T _{DSO}	MISO valid after Sclock driving edge	-	-	42 + 3 × T _{SCB}	ns
SID171A	T _{DSO_ext}	MISO valid after Sclock driving edge in Ext. Clock mode	-	-	48	ns
SID172	T _{HSO}	Previous MISO data hold time	0	-	-	ns
SID172A	T _{SSELSCK}	SSEL Valid to first SCK Valid edge	100	-	-	ns



Memory

Table 26. Flash DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID173	V _{PE}	Erase and program voltage	1.71	-	5.5	V	

Table 27. Flash AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID174	T _{ROWWRITE}	Row (block) write time (erase and program)	-	_	20	ms	Row (block) = 256 bytes
SID175	T _{ROWERASE}	Row erase time	-	-	13	ms	
SID176	T _{ROWPROGRAM}	Row program time after erase	-	-	7	ms	
SID178	T _{BULKERASE}	Bulk erase time (128 KB)	-	-	35	ms	
SID180	T _{DEVPROG}	Total device program time	-	_	15	seconds	Guaranteed by charac- terization
SID181	F _{END}	Flash endurance	100 K	_	_	cycles	Guaranteed by charac- terization
SID182	F _{RET}	Flash retention. $T_A \le 55 \text{ °C}$, 100 K P/E cycles	20	-	-	years	Guaranteed by charac- terization
SID182A		Flash retention. $T_A \leq 85~^\circ\text{C},~10~\text{K}$ P/E cycles	10	_	-	years	Guaranteed by charac- terization



System Resources

Power-on-Reset (POR) with Brown Out

Table 28. Imprecise Power On Reset (PRES)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID185	V _{RISEIPOR}	Rising trip voltage	0.80	_	1.45	V	Guaranteed by charac- terization
SID186	V _{FALLIPOR}	Falling trip voltage	0.75	_	1.4	V	Guaranteed by charac- terization
SID187	V _{IPORHYST}	Hysteresis	15	_	200	mV	Guaranteed by charac- terization

Table 29. Precise Power On Reset (POR)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID190	V _{FALLPPOR}	BOD trip voltage in active and sleep modes	1.64	-	-	V	Guaranteed by charac- terization
SID192	V _{FALLDPSLP}	BOD trip voltage in Deep Sleep	1.4	-	_	V	Guaranteed by charac- terization

Voltage Monitors

Table 30. Voltage Monitors DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID195	V _{LVI1}	LVI_A/D_SEL[3:0] = 0000b	1.71	1.75	1.79	V	
SID196	V _{LVI2}	LVI_A/D_SEL[3:0] = 0001b	1.76	1.80	1.85	V	
SID197	V _{LVI3}	LVI_A/D_SEL[3:0] = 0010b	1.85	1.90	1.95	V	
SID198	V _{LVI4}	LVI_A/D_SEL[3:0] = 0011b	1.95	2.00	2.05	V	
SID199	V _{LVI5}	LVI_A/D_SEL[3:0] = 0100b	2.05	2.10	2.15	V	
SID200	V _{LVI6}	LVI_A/D_SEL[3:0] = 0101b	2.15	2.20	2.26	V	
SID201	V _{LVI7}	LVI_A/D_SEL[3:0] = 0110b	2.24	2.30	2.36	V	
SID202	V _{LVI8}	LVI_A/D_SEL[3:0] = 0111b	2.34	2.40	2.46	V	
SID203	V _{LVI9}	LVI_A/D_SEL[3:0] = 1000b	2.44	2.50	2.56	V	
SID204	V _{LVI10}	LVI_A/D_SEL[3:0] = 1001b	2.54	2.60	2.67	V	
SID205	V _{LVI11}	LVI_A/D_SEL[3:0] = 1010b	2.63	2.70	2.77	V	
SID206	V _{LVI12}	LVI_A/D_SEL[3:0] = 1011b	2.73	2.80	2.87	V	
SID207	V _{LVI13}	LVI_A/D_SEL[3:0] = 1100b	2.83	2.90	2.97	V	
SID208	V _{LVI14}	LVI_A/D_SEL[3:0] = 1101b	2.93	3.00	3.08	V	
SID209	V _{LVI15}	LVI_A/D_SEL[3:0] = 1110b	3.12	3.20	3.28	V	
SID210	V _{LVI16}	LVI_A/D_SEL[3:0] = 1111b	4.39	4.50	4.61	V	
SID211	LVI_IDD	Block current	-	-	100	μA	Guaranteed by charac- terization

Table 31. Voltage Monitors AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID212	T _{MONTRIP}	Voltage monitor trip time	-	-	1		Guaranteed by charac- terization



SWD Interface

Table 32. SWD Interface Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID213	F_SWDCLK1	$3.3~V \le V_{DD} \le 5.5~V$	_	-	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	$1.71~V \le V_{DD} \le 3.3~V$	_	-	7	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID215	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	-	_	ns	Guaranteed by characterization
SID216	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	-	_	ns	Guaranteed by characterization
SID217	T_SWDO_VALID	T = 1/f SWDCLK	_	-	0.5*T	ns	Guaranteed by characterization
SID217A	T_SWDO_HOLD	T = 1/f SWDCLK	1	-	_	ns	Guaranteed by characterization

Internal Main Oscillator

Table 33. IMO DC Specifications

(Guaranteed by Design)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID218	I _{IMO1}	IMO operating current at 48 MHz	_	-	1000	μA	
SID219	I _{IMO2}	IMO operating current at 24 MHz	_	-	325	μA	
SID220	I _{IMO3}	IMO operating current at 12 MHz	-	-	225	μA	
SID221	I _{IMO4}	IMO operating current at 6 MHz	_	-	180	μA	
SID222	I _{IMO5}	IMO operating current at 3 MHz	_	-	150	μA	

Table 34. IMO AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID223	F _{IMOTOL1}	Frequency variation from 3 to 48 MHz	-	-	±2	%	
SID226	T _{STARTIMO}	IMO startup time	_	-	12	μs	
SID227	T _{JITRMSIMO1}	RMS Jitter at 3 MHz	_	156	-	ps	
SID228	T _{JITRMSIMO2}	RMS Jitter at 24 MHz	_	145	-	ps	
SID229	T _{JITRMSIMO3}	RMS Jitter at 48 MHz	_	139	_	ps	

Internal Low-Speed Oscillator

Table 35. ILO DC Specifications

(Guaranteed by Design)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID231	I _{ILO1}	ILO operating current at 32 kHz	-	0.3	1.05		Guaranteed by Characterization
SID233	IILOLEAK	ILO leakage current	-	2	15		Guaranteed by Design



Table 40. Watch Crystal Oscillator (WCO) Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
WCO Spec	ifications	<u>.</u>					
SID398 FWCO Crystal frequency				32.768	-	kHz	
SID399	FTOL	Frequency tolerance	-	50	250	ppm	With 20-ppm crystal.
SID400	ESR	Equivalent series resistance	-	50	-	kΩ	
SID401	PD	Drive Level		-	1	μW	
SID402	TSTART	Startup time	-	-	500	ms	
SID403	CL	Crystal load capacitance	6	-	12.5	pF	
SID404	SID404 C0 Crystal shunt capacitance		-	1.35	-	pF	
SID405	IWCO1	Operating current (high power mode)	_	-	8	uA	

Table 41. External Crystal Oscillator (ECO) Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID316	IECO1	Block operating current	-	-	1.5	mA	
SID317	FECO	Crystal frequency range	4	-	33	MHz	

Table 42. UDB AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
Datapath p	erformance						
SID249	F _{MAX-TIMER}	Max frequency of 16-bit timer in a UDB pair	-	-	48	MHz	
SID250				-	48	MHz	
SID251	F _{MAX_CRC}	Max frequency of 16-bit CRC/PRS in a UDB pair	-	-	48	MHz	
PLD Perfor	mance in UDB						
SID252	F _{MAX_PLD}	Max frequency of 2-pass PLD function in a UDB pair	-	-	48	MHz	
Clock to O	utput Performance						
SID253	T _{CLK_OUT_UDB1}	Prop. delay for clock in to data out at 25 °C, Typ.	-	15	-	ns	
SID254	T _{CLK_OUT_UDB2}	Prop. delay for clock in to data out, Worst case.	_	25	_	ns	



Table 43. Block Specs

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID256	T _{WS48}	Number of wait states at 48 MHz	2	-	-		CPU execution from Flash. Guaranteed by characterization
SID257	T _{WS24}	Number of wait states at 24 MHz	1	-	-		CPU execution from Flash. Guaranteed by characterization
SID260	V _{REFSAR}	Trimmed internal reference to SAR	-1		+1	%	Percentage of Vbg (1.024 V). Guaranteed by characterization
SID261	F _{SARINTREF}	SAR operating speed without external reference bypass	-	500	_	ksps	12-bit resolution. Guaranteed by characterization
SID262	T _{CLKSWITCH}	Clock switching from clk1 to clk2 in clk1 periods	3	-	4	Periods	Guaranteed by design
* Tws48 and T	Tws24 are guaranteed	l by Design					

Table 44. UDB Port Adaptor Specifications

(Based on LPC Component Specs; all specs except TLCLKDO are guaranteed by design -10-pF load, 3-V V_{DDIO} and V_{DDD})

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID263	T _{LCLKDO}	LCLK to output delay	_	-	18	ns	
SID264	T _{DINLCLK}	Input setup time to LCLCK rising edge	_	-	7	ns	
SID265	TDINLCLKHLD	Input hold time from LCLK rising edge	0	-	_	ns	
SID266	T _{LCLKHIZ}	LCLK to output tristated	-	-	28	ns	
SID267	T _{FLCLK}	LCLK frequency	-	-	33	MHz	
SID268	T _{LCLKDUTY}	LCLK duty cycle (percentage high)	40	-	60	%	

Table 45. USB Device Block Specifications (USB only)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
SID321	Vusb_5	Device supply for USB operation	4.5	-	5.5	V	USB Configured, USB Reg. enabled
SID322	Vusb_3.3	Device supply for USB operation	3.15	-	3.6	V	USB Configured, USB Reg. bypassed
SID323	Vusb_3.3	Device supply for USB operation (Functional operation only)	2.85	-	3.6	V	USB Configured, USB Reg. bypassed
SID324	lusb_config	Device supply current in Active mode, IMO = 24 MHz	-	10	-	mA	V _{DDD} = 5 V
SID325	lusb_config	Device supply current in Active mode, IMO = 24 MHz	-	8	-	mA	V _{DDD} = 3.3 V
SID326	Isub_suspend	Device supply current in Sleep mode	-	0.5	-	mA	V _{DDD} = 5 V, PICU wakeup
SID327	Isub_suspend	Device supply current in Sleep mode	-	0.3	-	mA	V _{DDD} = 5 V, Device disconnected
SID328	Isub_suspend	Device supply current in Sleep mode	-	0.5	-	mA	V _{DDD} = 3.3 V, PICU wakeup
SID329	Isub_suspend	Device supply current in Sleep mode	_	0.3	_	mA	V _{DDD} = 3.3 V, Device disconnected



Ordering Information

The PSoC 4200-L family part numbers and features are listed in the following table.

Table 48. PSoC 4200-L Ordering Information

								F	eatures								Pack	kage	
Category	NdW	Max CPU Speed (MHz)	Flash (KB)	SRAM (KB)	UDB	Op-amp (CTBm)	CSD	Direct LCD Drive	12-bit SAR ADC	LP Comparators	TCPWM Blocks	SCB Blocks	USB Full Speed	CAN	GPIO	48-TQFP	64-TQFP	68-QFN	124-VFBGA
	CY8C4246AZI-L423	48	64	8	8	2	1	>	1000 ksps	2	8	3	-	١	38	>	Ι	-	-
	CY8C4246AZI-L433	48	64	8	8	2	Ι	-	1000 ksps	2	8	3	<	-	38	1	Ι	Ι	-
4246	CY8C4246AZI-L435	48	64	8	8	2	-	-	1000 ksps	2	8	4	<	-	53	-	<	-	-
	CY8C4246AZI-L445	48	64	8	8	2	2	~	1000 ksps	2	8	4	<	-	53	-	<	-	-
	CY8C4246LTI-L445	48	64	8	8	2	2	~	1000 ksps	2	8	4	~	-	57	-	-	~	-
	CY8C4247AZI-L423	48	128	16	8	2	1	~	1000 ksps	2	8	3	-	-	38	~	-	-	-
	CY8C4247AZI-L433	48	128	16	8	2	-	_	1000 ksps	2	8	3	~	_	38	~	-	-	-
	CY8C4247AZI-L445	48	128	16	8	2	2	~	1000 ksps	2	8	4	~		53	Ι	~	-	-
	CY8C4247LTI-L445	48	128	16	8	2	2	>	1000 ksps	2	8	4	~	-	57	Ι	-	~	-
4247	CY8C4247AZI-L475	48	128	16	8	4	2	-	1000 ksps	2	8	4	~	-	53	Ι	~	-	-
4247	CY8C4247LTI-L475	48	128	16	8	4	2		1000 ksps	2	8	4	~	-	57	Ι	-	~	-
	CY8C4247BZI-L479	48	128	16	8	4	2	-	1000 ksps	2	8	4	~	-	98	-	-	-	~
	CY8C4247AZI-L485	48	128	16	8	4	2	>	1000 ksps	2	8	4	~	>	53	Ι	~	-	-
	CY8C4247LTI-L485	48	128	16	8	4	2	>	1000 ksps	2	8	4	~	>	57	Ι	-	~	-
	CY8C4247BZI-L489	48	128	16	8	4	2	>	1000 ksps	2	8	4	~	>	98	-	-	-	~
	CY8C4248BZI-L469	48	256	32	8	4	Ι	-	1000 ksps	2	8	4	-	-	96	Ι	-	-	~
	CY8C4248AZI-L475	48	256	32	8	4	2	-	1000 ksps	2	8	4	~	-	53	-	~	-	-
	CY8C4248LTI-L475	48	256	32	8	4	2	_	1000 ksps	2	8	4	~	_	57	_	-	~	-
4248	CY8C4248BZI-L479	48	256	32	8	4	2	_	1000 ksps	2	8	4	~	_	98	-	-	-	~
	CY8C4248AZI-L485	48	256	32	8	4	2	~	1000 ksps	2	8	4	~	~	53	_	~	-	-
	CY8C4248LTI-L485	48	256	32	8	4	2	~	1000 ksps	2	8	4	~	~	57	_	-	~	-
	CY8C4248BZI-L489	48	256	32	8	4	2	>	1000 ksps	2	8	4	~	>	98	Ι	-	-	~

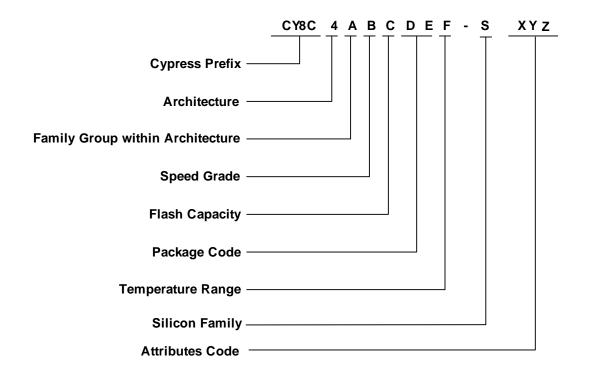


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The nomenciature used in	Table 40 IS Dased	i on me ioliowino pari r	iumbenna conveniion.

Field	Description	Values	Meaning
CY8C	Cypress Prefix		
4	Architecture	4	PSoC 4
Α	Family	2	4200 Family
В	CPU Speed	4	48 MHz
С	Flash Capacity	6	64 KB
		7	128 KB
		8	256 KB
DE	Package Code	AX, AZ	TQFP
		LT	QFN
		BU	BGA
		FD	CSP
F	Temperature Range	I	Industrial
S	Silicon Family	N/A	PSoC 4A
		L	PSoC 4A-L
		BL	PSoC 4A-BLE
XYZ	Attributes Code	000-999	Code of feature set in the specific family

Part Numbering Conventions

The part number fields are defined as follows.





Packaging

The description of the PSoC4200-L package dimensions follows.

SPEC ID#	Package	Description	Package DWG #
PKG_1	124-ball VFBGA	124-ball, 9 mm x 9 mm x 1.0 mm height with 0.65 mm ball pitch	001-97718
PKG_2	64-pin TQFP	64-pin TQFP, 10 mm x10 mm x 1,4 mm height with 0.5 mm pitch	51-85051
PKG_3	68-pin QFN	68-pin QFN, 8 mm x 8 mm x 1.0 mm height with 0.4 mm pitch	001-09618
PKG_4	48-pin TQFP	48-pin TQFP, 7 mm x 7 mm x 1.4 mm height with 0.5 mm pitch	51-85135

Table 49. Package Characteristics

Parameter	Description	Conditions	Min	Тур	Max	Units
T _A	Operating ambient temperature		-40	25.00	85	°C
TJ	Operating junction temperature		-40	-	100	°C
T _{JA}	Package θ_{JA} (124-ball VFBGA)		-	35	-	°C/Watt
T _{JA}	Package θ_{JA} (64-pin TQFP)		-	54	-	°C/Watt
T _{JA}	Package θ_{JA} (68-pin QFN)		-	17	-	°C/Watt
T _{JA}	Package θ_{JA} (48-pin TQFP)		_	67	_	°C/Watt

Table 50. Solder Reflow Peak Temperature

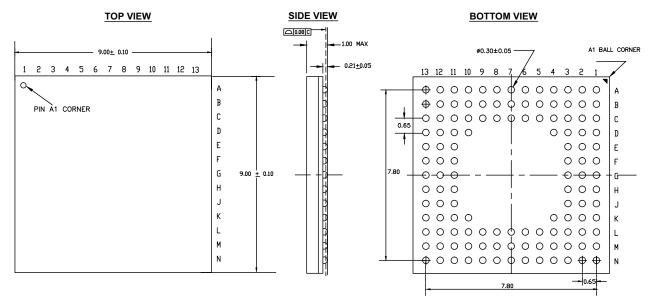
Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
All packages	260 °C	30 seconds

Table 51. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-2

Package	MSL
All packages	MSL 3



Figure 8. 124-Ball VFBGA Package Outline



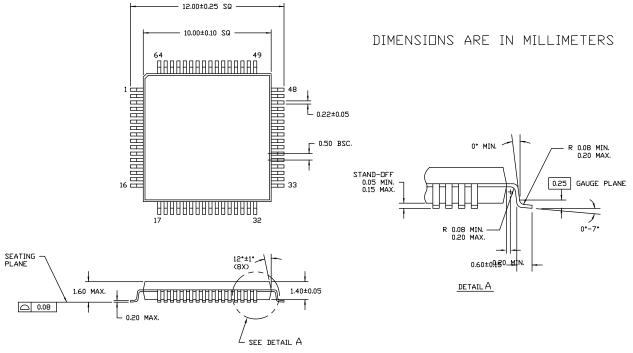
NOTES:

1. REFERENCE JEDEC # MO-280

2. ALL DIMENSIONS ARE IN MILLIMETERS

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Table 52. Acronyms Used in this Document (continued)

Acronym	Description	
PC	program counter	
PCB	printed circuit board	
PGA	programmable gain amplifier	
PHUB	peripheral hub	
PHY	physical layer	
PICU	port interrupt control unit	
PLA	programmable logic array	
PLD	programmable logic device, see also PAL	
PLL	phase-locked loop	
PMDD	package material declaration data sheet	
POR	power-on reset	
PRES	precise power-on reset	
PRS	pseudo random sequence	
PS	port read data register	
PSoC [®]	Programmable System-on-Chip™	
PSRR	power supply rejection ratio	
PWM	pulse-width modulator	
RAM	random-access memory	
RISC	reduced-instruction-set computing	
RMS	root-mean-square	
RTC	real-time clock	
RTL	register transfer language	
RTR	remote transmission request	
RX	receive	
SAR	successive approximation register	
SC/CT	switched capacitor/continuous time	
SCL	I ² C serial clock	
SDA	I ² C serial data	
S/H	sample and hold	
SINAD	signal to noise and distortion ratio	
SIO	special input/output, GPIO with advanced features. See GPIO.	
SOC	start of conversion	
SOF	start of frame	
SPI	Serial Peripheral Interface, a communications protocol	
SR	slew rate	
SRAM	static random access memory	
SRES	software reset	
SWD	serial wire debug, a test protocol	

Table 52. Acronyms Used in this Document (continued)

Acronym	Description
SWV	single-wire viewer
TD	transaction descriptor, see also DMA
THD	total harmonic distortion
TIA	transimpedance amplifier
TRM	technical reference manual
TTL	transistor-transistor logic
TX	transmit
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
UDB	universal digital block
USB	Universal Serial Bus
USBIO	USB input/output, PSoC pins used to connect to a USB port
VDAC	voltage DAC, see also DAC, IDAC
WDT	watchdog timer
WOL	write once latch, see also NVL
WRES	watchdog timer reset
XRES	external reset I/O pin
XTAL	crystal